

**DISCRIPTION**

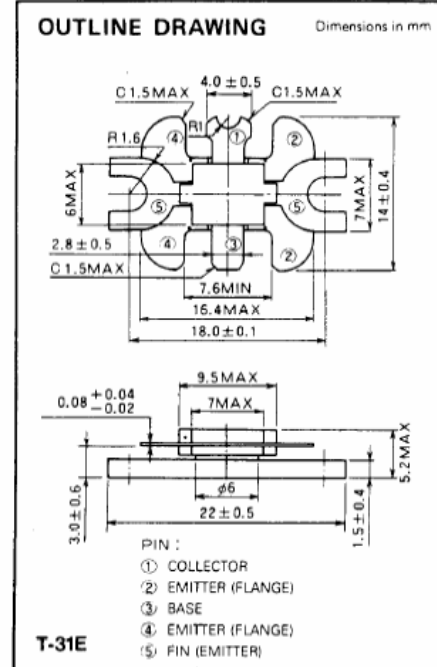
2SC1946 is a silicon NPN epitaxial planar type transistor designed for RF power amplifiers on VHF band mobile radio applications.

**FEATURES**

- High power gain:  $G_{pe} \geq 6.7\text{dB}$   
@  $V_{CC} = 13.5\text{V}$ ,  $P_O = 28\text{W}$ ,  $f = 175\text{MHz}$
- Emitter ballasted construction and gold metallization for high reliability and good performances.
- Low thermal resistance ceramic package with flange.
- Ability of withstanding more than 20:1 load VSWR when operated at  $V_{CC} = 15.2\text{V}$ ,  $P_O = 30\text{W}$ ,  $f = 175\text{MHz}$ .

**APPLICATION**

25 watts output power amplifiers applications in VHF band.



**ABSOLUTE MAXIMUM RATINGS** ( $T_C = 25^\circ\text{C}$  unless otherwise specified)

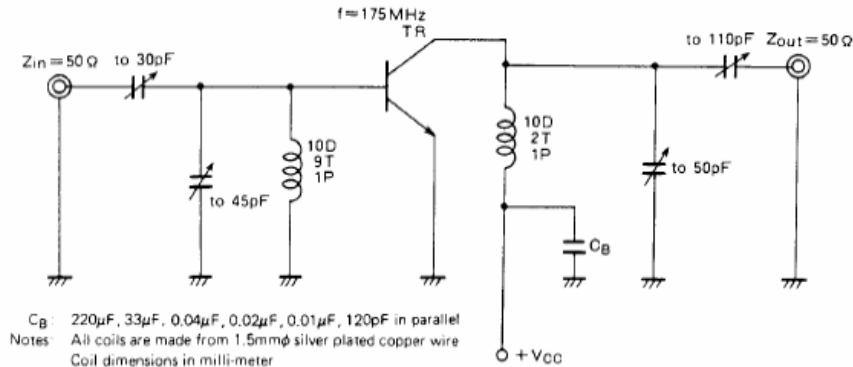
Symbol	Parameter	Conditions	Ratings	Unit
$V_{CBO}$	Collector to base voltage		35	V
$V_{EBO}$	Emitter to base voltage		4	V
$V_{CEO}$	Collector to emitter voltage	$R_{BE} = \infty$	17	V
$I_C$	Collector current		7	A
$P_C$	Collector dissipation	$T_a = 25^\circ\text{C}$	3	W
		$T_C = 25^\circ\text{C}$	50	W
$T_j$	Junction temperature		175	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-65 to 175	$^\circ\text{C}$
$R_{th-a}$	Thermal resistance	Junction to ambient	50	$^\circ\text{C/W}$
$R_{th-c}$		Junction to case	3	$^\circ\text{C/W}$

Note. Above parameters are guaranteed independently.

**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)EBO}$	Emitter to base breakdown voltage	$I_E = 10\text{mA}$ , $I_C = 0$	4			V
$V_{(BR)CBO}$	Collector to base breakdown voltage	$I_C = 10\text{mA}$ , $I_E = 0$	35			V
$V_{(BR)CEO}$	Collector to emitter breakdown voltage	$I_C = 100\text{mA}$ , $R_{BE} = \infty$	17			V
$I_{CBO}$	Collector cutoff current	$V_{CB} = 25\text{V}$ , $I_E = 0$			2	mA
$I_{EBO}$	Emitter cutoff current	$V_{EB} = 3\text{V}$ , $I_C = 0$			1	mA
$h_{FE}$	DC forward current gain*	$V_{CE} = 10\text{V}$ , $I_C = 0.2\text{A}$	10	50	180	—
$P_O$	Output power	$V_{CC} = 13.5\text{V}$ , $P_{in} = 6\text{W}$ , $f = 175\text{MHz}$	28	32		W
$\eta_C$	Collector efficiency		60	70		%

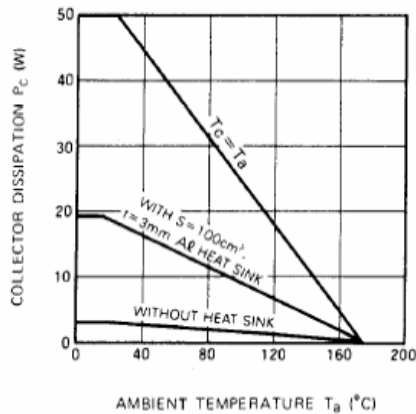
TEST CIRCUIT



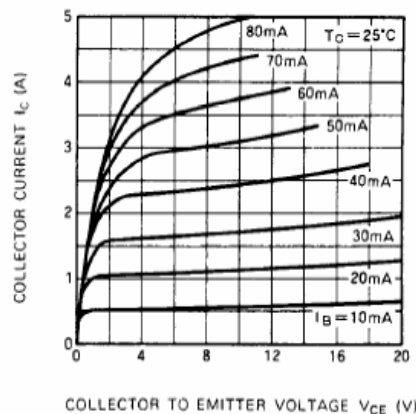
$C_B$ : 220 $\mu$ F, 33 $\mu$ F, 0.04 $\mu$ F, 0.02 $\mu$ F, 0.01 $\mu$ F, 120pF in parallel  
 Notes: All coils are made from 1.5mm $\phi$  silver plated copper wire  
 Coil dimensions in milli-meter  
 D: Inner diameter of coil  
 T: Turn number of coil  
 P: Pitch of coil

TYPICAL PERFORMANCE DATA

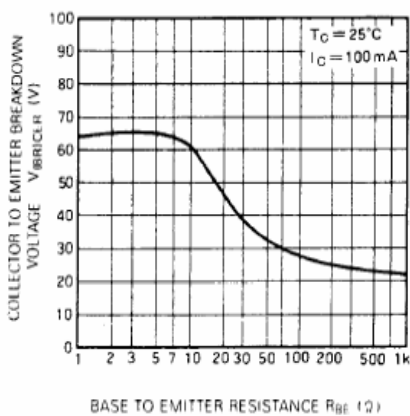
COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE



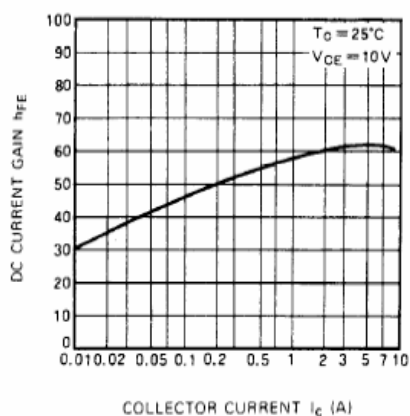
COLLECTOR CURRENT VS. COLLECTOR TO EMITTER VOLTAGE



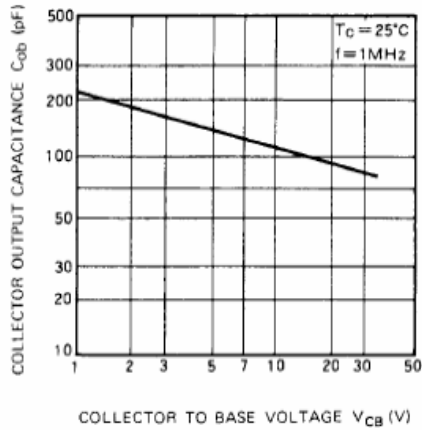
COLLECTOR TO EMITTER BREAKDOWN VOLTAGE VS. BASE TO EMITTER RESISTANCE



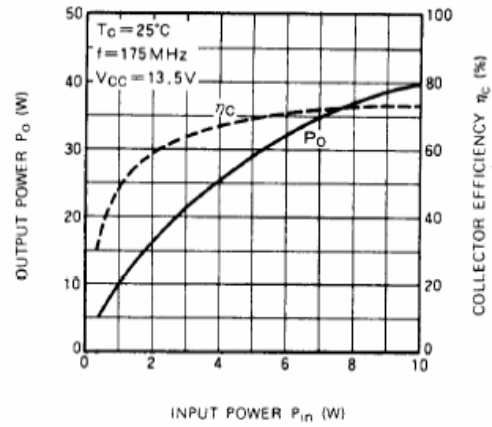
DC CURRENT GAIN VS. COLLECTOR CURRENT



COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE



OUTPUT POWER, COLLECTOR EFFICIENCY VS. INPUT POWER



OUTPUT POWER VS. COLLECTOR SUPPLY VOLTAGE

